

Essentials of MOSFETs

Lecture 5.2: Power MOSFETs

Short Problem

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Assume a Si power MOSFET with a specific on resistance of $10 \text{ m}\Omega\text{-cm}^2$ and a drift layer doping density of $N_D = 10^{15} \text{ cm}^{-3}$.

- 1) What is the expected breakdown voltage for this device?